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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Kenji MARUYAMA**

Group Art Unit: **2813**

Serial No.: **09/960,296**

Examiner: **L. SCHILLINGER**

Filed: **September 24, 2001**

Confirmation No.: **4754**

For: **SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING
THE SAME**

Attorney Docket Number: **011267**

Customer Number: **38834**

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 C.F.R. §1.97(c)(1)

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

August 23, 2004

Sir:

Applicants direct the attention of the Patent and Trademark Office to the documents listed on the attached Form PTO-1449. A copy of each listed document is attached.

This Information Disclosure Statement is being submitted after issuance of a first official action on the merits and expiration of the three month period following the filing date or the entry of the national stage for the above-captioned application, but prior to issuance of either a final official action or a Notice of Allowance.

The undersigned hereby certifies that each item of information contained in the Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the Information Disclosure Statement.

Information Disclosure Statement under 1.97(c)(1)
Attorney Docket No. 011267
Serial No. 09/960,296

The Commissioner is authorized to charge our Deposit Account No. 50-2866 for any fee
that is required to effect consideration of this statement.

Respectfully submitted,

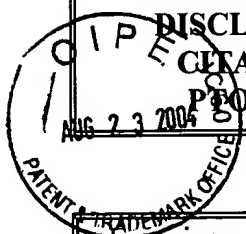
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Enclosures: PTO-1449
References



INFORMATION DISCLOSURE CITATION PTO-1449	Attorney Docket Number. 011267	Serial No. 09/960,296
	Applicant(s): Kenji MARUYAMA et al.	
	Filing Date: September 24, 2001	Group Art Unit: 2813

U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
	5,781,404	Summerfelt et al.	7/14/98	361	321.5	6/7/95

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document No.	Date	Country	Translation (Yes or No)
	0 568 064 A2	11/3/93	EP	
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	0 920 054 A1	6/2/99	EP	

OTHER DOCUMENTS

	<p>Suk Shin et al.: "Characteristics of Pt/SrTi03/Pb(Zr0.52,Ti0.48)03/SrTi03/Si Ferroelectric Gate Oxide Structure", Preparation and Characterization, Elsevier Sequoia, NL, vol. 354, no. 1-2, October 8, 1999, pgs.251-255, XP004321418 ISSN: 0040-6090, abstract; figure 2; table 1.</p> <p>Lee Chang et al.: "Single and Multilayer Ferroelectric PbZrxTi1-x03 (PZT) on BaTi03", Thin Solid Films, Elsevier-Sequoia S.A. Lausanne, CH., vol. 303, no. 1-2, July 15, 1997, pgs. 94-100, XP004087618 ISSN: 0040-6090, page 98, paragraph 2; figure 5.</p> <p>Inoue et al.: "Low Thermal-Budget Fabrication of Sputtered-PZT Capacitor on Multilevel Interconnects for Embedded FeRAM, Silicon Systems REs. Labs. And ULSI Development Div., NEC 2000 IEEE</p> <p>Communication from European Patent Office dated June 6, 2004 and European Search Report dated June 4, 2004</p>
Examiner	Date Considered